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925
PATENT 9/10/03
J. Carter

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl No. : 09/994,511

Applicants : Kie Y. Ahn; Leonard Forbes

Filed : November 26, 2001

Art Unit : 2879

Examiner : Kenneth J. Ramsey

Title : FIELD EMISSION DISPLAY HAVING REDUCED POWER REQUIREMENTS AND
METHOD

Confirmation No. : 1533

Attorney Docket No.: 500466.02 (29356/US/1)

Customer No. : 27,076

Issue Fee Paid : July 3, 2003

INFORMATION DISCLOSURE STATEMENT

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OFFICE OF PETITIONS

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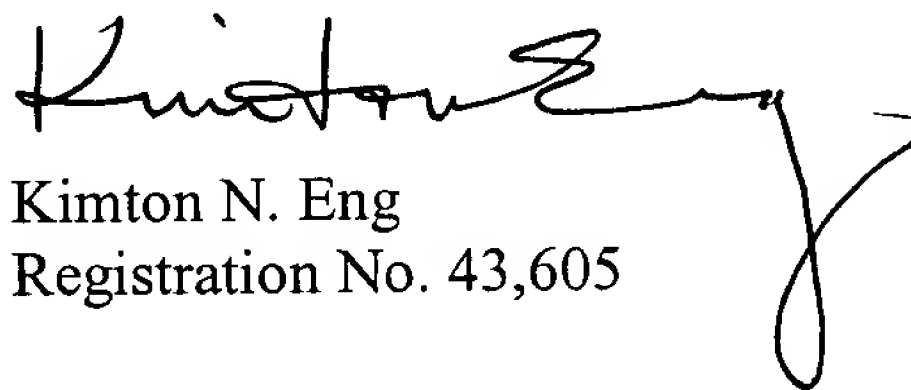
Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97 through 1.98, applicants wish to make known to the Patent and Trademark Office the references set forth on the attached form PTO-1449 (copies of the cited references, as required under 37 C.F.R. § 1.98, are enclosed). Although the aforesaid references are made known to the Patent and Trademark Office in compliance with applicants' duty to disclose all information they are aware of which is believed relevant to the examination of the above-identified application, applicants believe that their invention is patentable.

Please acknowledge receipt of this Information Disclosure Statement and kindly make the cited references of record in the above-identified application.

Respectfully submitted,

DORSEY & WHITNEY LLP



Kimton N. Eng
Registration No. 43,605

SHA:mp/pep

Enclosures:

Form PTO-1449
Cited References (37)

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FORM PTO-1449 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 500466.02		APPLICATION NO. 09/994,511	
INFORMATION DISCLOSURE STATEMENT <i>(Use several sheets if necessary)</i>				APPLICANT(S) Kie Y Ahn; Leonard Forbes			
				FILING DATE November 26, 2001		GROUP ART UNIT 2879	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
AA	3,665,241	05/23/72	Spindt et al.	313	351		
AB	3,755,704	08/28/73	Spindt et al.	313	309		
AC	3,812,559	05/28/74	Spindt et al.	29	25		
AD	4,266,233	05/05/81	Bertotti et al.	357	22		
AE	5,142,184	8/25/92	Kane	313	309		
AF	5,194,780	3/16/93	Meyer	315	169.3		
AG	5,229,331	07/20/93	Doan et al.	437	228		
AH	5,259,799	11/09/93	Doan et al.	445	24		
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AQ	5,712,534	1/27/98	Lee et al.	315	169.3		

FOREIGN PATENT DOCUMENTS							
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION		
					YES	NO	
AR							

OTHER PRIOR ART <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>	
AS	Anderson, R.C. et al., "Porous Polycrystalline Silicon: A New Material for MEMS," <i>Journal of Microelectromechanical Systems</i> 3(1):10-18, 1994
AT	Boswell, E.C. et al., "Polycrystalline Silicon Field Emitters," 8 th International Vacuum Microelectronics Conference Technical Digest, pp. 181-186, 1996

EXAMINER	DATE CONSIDERED

* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

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OTHER PRIOR ART <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>					
	BA	Boswell, E.C. et al., "Polycrystalline silicon field emitters," <i>J Vac Sci Technol. B</i> 14(3):1910-1913, 1996			
	BB	Huang, W.N. et al., "Photoluminescence in porous sputtered polysilicon films formed by chemical etching," <i>Semicond. Sci. Technol.</i> 12:228-233, 1997			
	BC	Huang, W.N. et al., "Properties of chemically etched porous polycrystalline silicon deposited by r.f. sputtering," IEEE Hong Kong Electron Devices Meeting, pp. 21-24, 1996			
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	BJ	Lazarouk, S. et al., "Electrical characterization of visible emitting electroluminescent Schottky diodes based on n-type porous silicon and on highly doped n-type porous polysilicon," <i>Journal of Non-Crystalline Solids</i> 198-200:973-976, 1996			
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	BL	Lee, K.R. et al., "Field emission behavior of (nitrogen incorporated) diamond-like carbon films," <i>Thin Solid Films</i> 290-291:171-175, 1996			
	BM	Litovchenko, V.G. et al., "Emission Properties of the Silicon Cathodes Coated with Doped Diamond-Like Carbon Films," IEEE International Conf. On Plasma Science, p. 308, Abstract 7A02, 1997			
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	BP	Uh, H.S. et al., "Fabrication and Characterization of Gated n+ Polycrystalline Silicon Field Emitter Arrays," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 419-422, 1996			
	BQ	Uh, H.S., "Process design and emission properties of gated n+ polycrystalline silicon field emitter arrays for flat-panel display applications," <i>J. Vac. Sci. Technol. B</i> 15(2):472-476, 1997			
	BR	Vaudaine, P. and Meyer, R., "Microtips Fluorescent Display," technical digest of IEDM 91, pp. 197-200, 1991			
EXAMINER				DATE CONSIDERED	
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